N-Channel 200 V (D-S) Power MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
200	700 at V _{GS} = 10 V	1.5	16 nC			

FEATURES

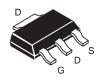
- DT-Trench Power MOSFET
- Super Low Gate Charge
- Excellent gate charge x R_{DS(on)} product(FOM)



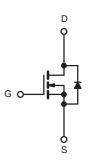
APPLICATIONS

- Power switching application
- · Hard switched and high frequency circuits

SOT-223 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V_{DS}	200	V		
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _C = 25 °C	1	1.5			
Continuous Diam Curient (1) = 150 C)	T _C = 100 °C	I _D	1.07	Α		
Pulsed Drain Current ^b		I _{DM}	6			
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	12.5 ^c	w		
Maximum Fower Dissipation	T _C = 100 °C	י ט	5			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	- °C		
Soldering Recommendations (Peak Temperature)			260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^d	t ≤ 10 s	R_{thJA}	-	85	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	-	10	0, 11	

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{BJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	=	± 100	nA
		V _{DS} = 200 V, V _{GS} = 0 V	-	-	1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125°C	-	-	100	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	1.5	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 1 A	-	700	840	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 1 A	-	10	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	856	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1MHz	-	122	-	
Reverse Transfer Capacitance	C _{rss}		-	4.6	-	
Total Gate Charge ^c	Qg		-	16	-	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$	-	3	-	nC
Gate-Drain Charge ^c	Q _{gd}		=	8	-	
Gate Resistance	R_g	f = 1 MHz	-	2.5	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	25	-	
Rise Time ^c	t _r	$V_{DD} = 100 \text{ V}, I_D = 1 \text{ A},$	-	33	-	ns
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 3 \Omega$	-	51	-	
Fall Time ^c	t _f		-	13	-	
Drain-Source Body Diode Ratings an	nd Characteri	stics ^b (T _C = 25 °C)				
Continuous Source Current	I _S	T _C = 25 °C	-	-	1.5	Α
Pulsed Source Current	I _{SM}		-	-	6	Α
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V
Reverse Recovery Time t _{rr}		I _F = 1 A, di/dt = 100 A/μs	-	80	-	ns
Reverse Recovery Charge	Q _{rr}	i _F = 1 A, αί/αι = 100 Α/μS	-	219	-	nC

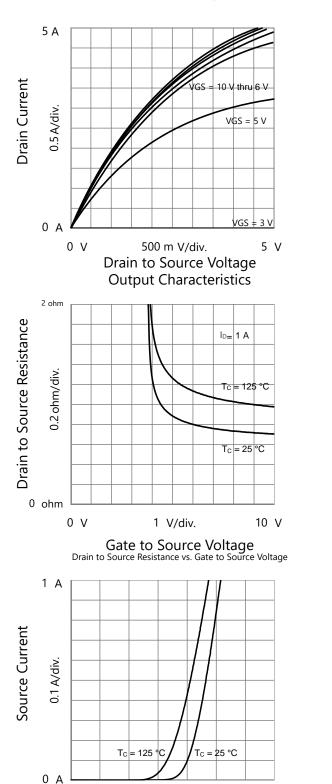
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

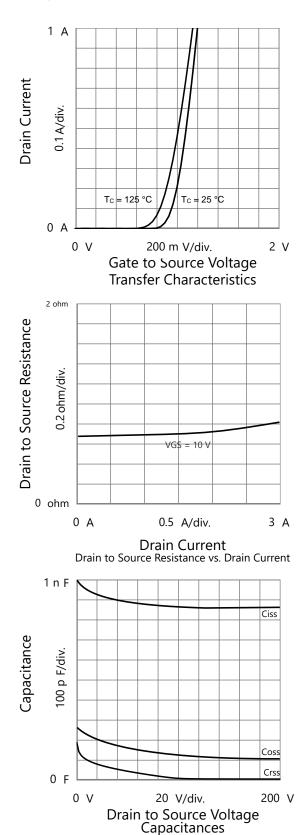


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



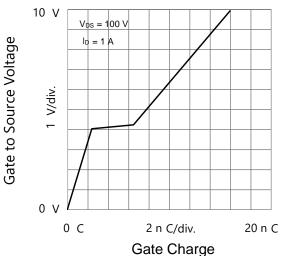
200 m V/div. Source to Drain Voltage Body Diode Forward Characteristics

0 V

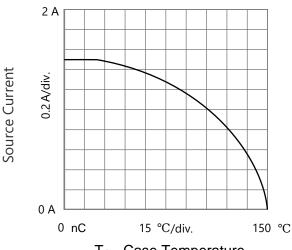




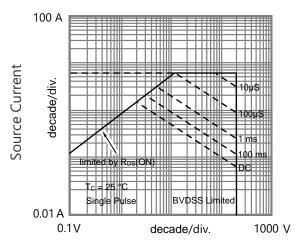
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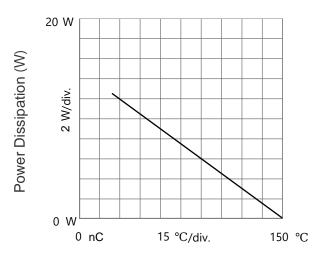
Gate to Source Voltage vs. GateCharge



 $T_{C} \textbf{ - Case Temperature}_{\text{Current Derating}}$

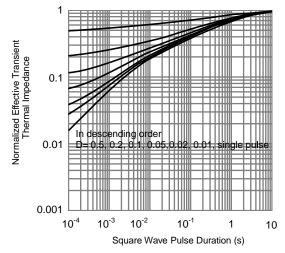


Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature

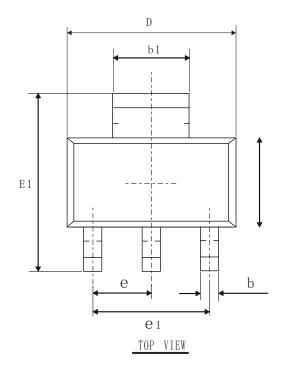
Current Derating

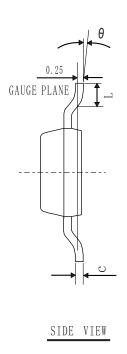


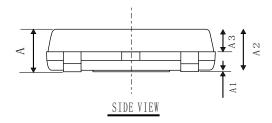
Normalized Thermal Transient Impedance



SOT-223-3L PACKAGE OUTLINE







COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	
Α	1	-	1.95	
A1	0.00	0.05	0.16	
A2	1.35	1.60	1.85	
A3	0.65	0.90	1.15	
b	0.55	0.70	0.90	
b1	2.75	3.00	3.30	
С	0.18	0.30	0.42	
D	6.00	6.50	7.00	
Е	3.10	3.50	3.90	
E1	6.50	7.00	7.50	
e1	4.20	4.60	5.00	
L	0.78	-	1.28	
θ	0°	5°	10°	
е	2.3BSC			





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